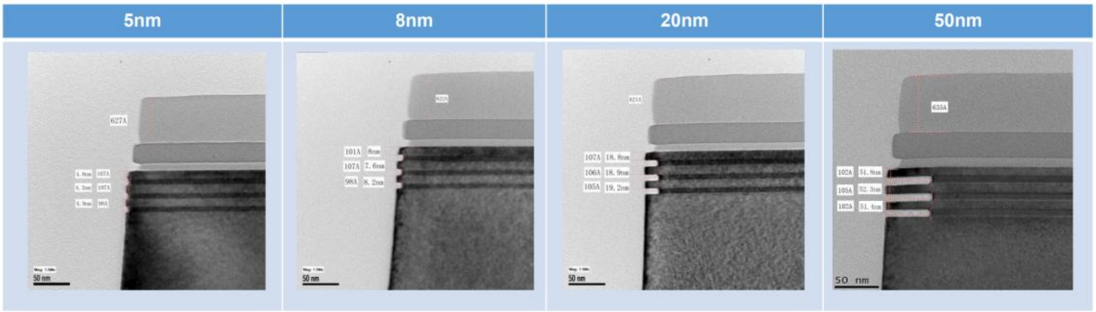


Fig1 Transmission electron microscopy profiles（TEM） with different etching depths

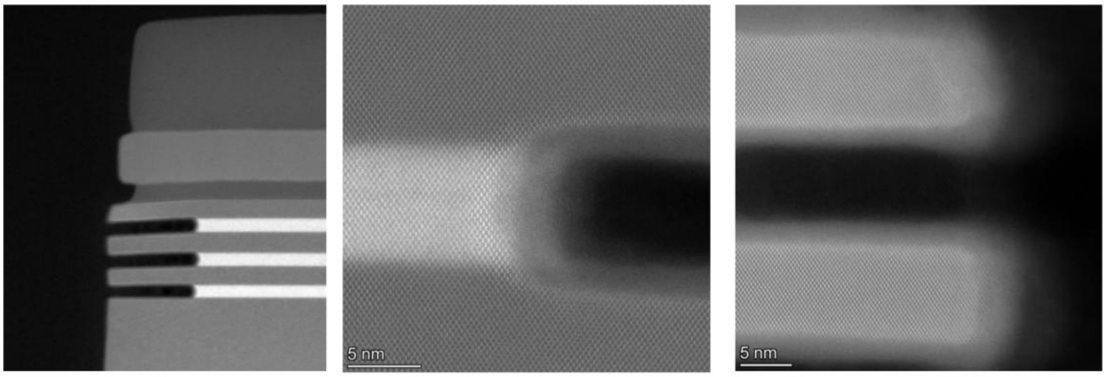


Fig2 High resolution TEM of RPS（Remote Plasma）selective etching SiGe

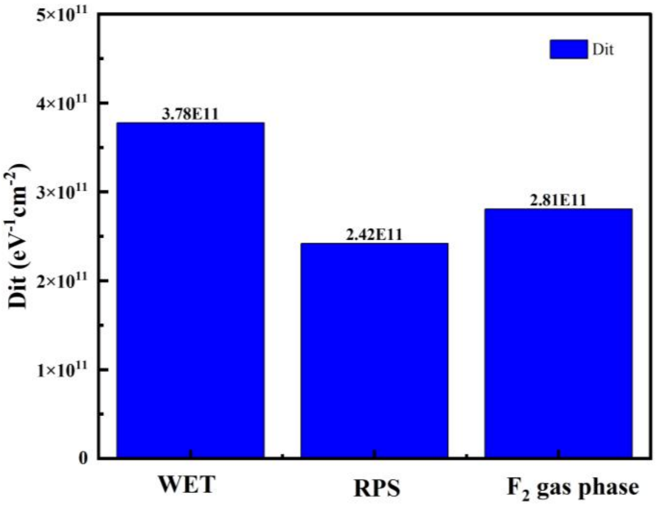
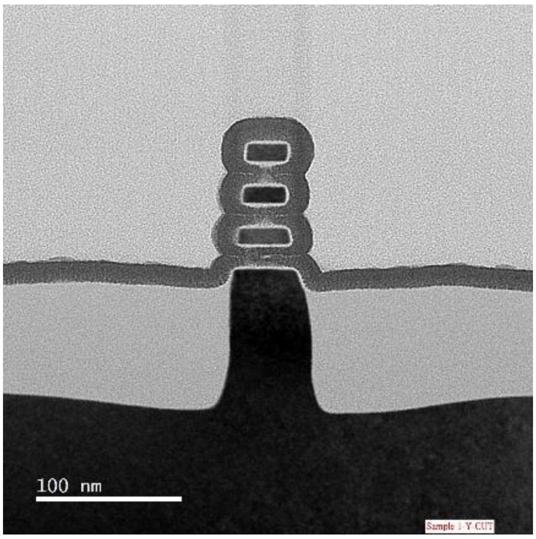


Fig3 Comparison of interface trap density (Dit) after selective etching of different SiGe methods



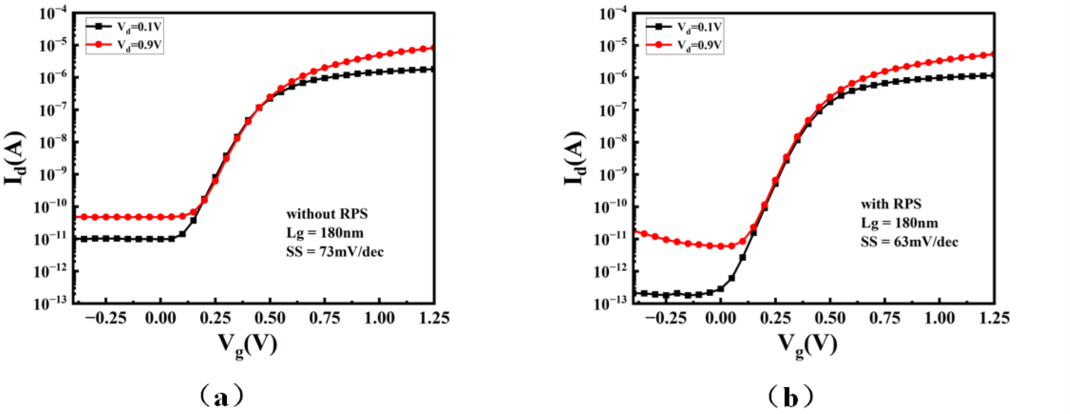


Fig4 Gate all around devices and electrical curves prepared using RPS channel release